

Promoting sensitivity and selectivity of HCHO sensor based on strained InP₃ monolayer: A DFT study

PII: S0169-4332(18)32133-0
 DOI: <https://doi.org/10.1016/j.apsusc.2018.08.014>
 Reference: APSUSC 40051

Received Date: 24 April 2018
Revised Date: 22 July 2018
Accepted Date: 1 August 2018

This is a PDF file of an unedited manuscript that has been accepted for publication. As a service to our customers we are providing this early version of the manuscript. The manuscript will undergo copyediting, typesetting, and review of the resulting proof before it is published in its final form. Please note that during the production process errors may be discovered which could affect the content, and all legal disclaimers that apply to the journal pertain.



Promoting sensitivity and selectivity of HCHO sensor based on strained InP₃ monolayer: A DFT study

Huiru Yang,¹ Zeping Wang,¹ and Huaiyu Ye,^{*1,2} Kai Zhang,^{*3} Xianping Chen,^{1,2} Guoqi Zhang²

¹Key Laboratory of Optoelectronic Technology & Systems, Education Ministry of China, College of Opto-electronic Engineering, Chongqing University, Chongqing 400044, China.

²Electronic Components, Technology and Materials, Delft University of Technology, 2628 CD Delft, The Netherlands.

³School of Electro-mechanical Engineering, Guangdong University of Technology, No.100 Waihuan Xi Road, Guangzhou Higher Education Mega Center, Guangzhou, 510006, China.

*Corresponding authors: huaiyu@tudelft.nl; zhangkai@gdut.edu.cn.

Download English Version:

<https://daneshyari.com/en/article/7832872>

Download Persian Version:

<https://daneshyari.com/article/7832872>

[Daneshyari.com](https://daneshyari.com)